

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katoh, T. et al.

Serial No.: 09/711,504

Group Art Unit: 2826

Filed: November 14, 2000

Examiner: Sefer, A.

For: THIN FILM TRANSISTOR AND FABRICATION METHOD OF THE SAME

Honorable Assistant Commissioner of Patents  
Washington, D.C. 20231

**EXCESS CLAIM FEE PAYMENT LETTER**

Sir:

Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

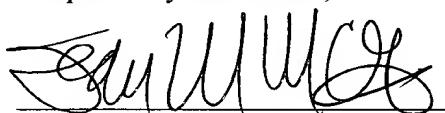
	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	18 -	20	= 0	x \$18.00	\$ 00.00
Indep. Claims	6 -	3	= 3	x \$84.00	\$ 252.00
<b>TOTAL ADDITIONAL FEE FOR THIS AMENDMENT</b>					<b>\$ 252.00</b>

A check in the amount of \$ 252.00 is herewith enclosed to cover the excess claim fees. A duplicate copy of this sheet is enclosed.

Respectfully Submitted,

Date:

7/8/02



Sean M. McGinn

Reg. No. 34,386

**McGinn & Gibb, PLLC**  
8321 Old Courthouse Rd. Suite 200  
Vienna, VA 2218-3817  
(703) 761-4100  
**Customer No. 21254**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katoh, T. et al.

Serial No.: 09/711,504

Filed: November 14, 2000

For: THIN FILM TRANSISTOR AND FABRICATION METHOD OF THE SAME

Honorable Commissioner of Patents  
Washington, D.C. 20231



Group Art Unit: 2826

Examiner: Sefer, A.

#9/A  
Am. 1  
J. McMillan  
RECEIVED  
JUL 12 2002  
TECHNOLOGY CENTER 2800

**AMENDMENT UNDER 37 C.F.R. §1.111**

Sir:

In response to the Office Action dated February 7, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 8-12 without prejudice or disclaimer.

Please amend the claims as follows.

1 1. (Amended) A thin film transistor including:  
2 a back channel electrode, wherein a voltage of a front channel positioned on the side  
3 of a gate wiring of said thin film transistor is made equal to a voltage of said back channel  
4 positioned on the side of a back channel electrode by short-circuiting said back channel  
5 electrode to a gate electrode through a contact-hole provided in a portion of a semiconductor  
6 layer forming said thin film transistor.

5. (Amended) A thin film transistor as claimed in claim 1, wherein a passivation film  
patterned to have a width equal to that of said back channel electrode and said semiconductor  
layer are provided between said back channel and a gate insulating film.